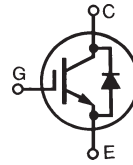


# GenX3™ 600V IGBT w/Diode

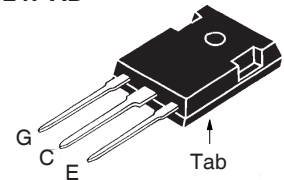
## IXGH48N60A3D1

$V_{CES} = 600V$   
 $I_{C110} = 48A$   
 $V_{CE(sat)} \leq 1.35V$

Ultra Low  $V_{sat}$  PT IGBT for  
up to 5kHz switching



TO-247 AD



G = Gate            C = Collector  
E = Emitter        Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_C = 25^\circ C$ to $150^\circ C$	600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C110}$	$T_C = 110^\circ C$	48	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	300	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 5\Omega$ Clamped inductive load	$I_{CM} = 96$ @ $\leq V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	300	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062in.) from case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic body for 10 seconds	260	$^\circ C$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		6	g

### Features

- Optimized for Low Conduction Losses
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- High Current Handling Capability
- International Standard Package

### Advantages

- High Power Density
- Low Gate Drive Requirement

### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ( $T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.5 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			300 $\mu A$ 1.75 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 32A$ , $V_{GE} = 15V$ , Note 1		1.18	1.35 V

### Symbol Test Conditions

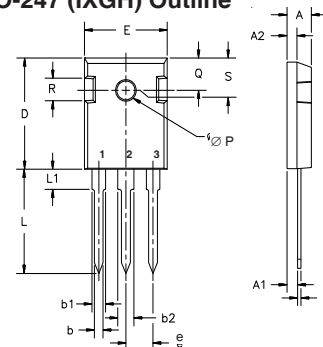
( $T_J = 25^\circ\text{C}$  unless otherwise specified)

### Characteristic Values

Min. Typ. Max.

Symbol	Test Conditions	Min.	Typ.	Max.
$g_{fs}$	$I_C = 32\text{A}, V_{CE} = 10\text{V}$ , Note 1	30	48	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3190	pF
$C_{oes}$			175	pF
$C_{res}$			43	pF
$Q_g$	$I_C = 32\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		110	nC
$Q_{ge}$			21	nC
$Q_{gc}$			42	nC
$t_{d(on)}$	<b>Inductive Load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 32\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		25	ns
$t_{ri}$			30	ns
$E_{on}$			0.95	mJ
$t_{d(off)}$			334	ns
$t_{fi}$			224	ns
$E_{off}$			2.9	mJ
$t_{d(on)}$	<b>Inductive Load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 32\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		24	ns
$t_{ri}$			30	ns
$E_{on}$			1.97	mJ
$t_{d(off)}$			545	ns
$t_{fi}$			380	ns
$E_{off}$			5.6	mJ
$R_{thJC}$				0.42 $^\circ\text{C/W}$
$R_{thCS}$		0.21		$^\circ\text{C/W}$

### TO-247 (IXGH) Outline



Terminals: 1 - Gate 2 - Collector  
3 - Emitter

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

### Reverse Diode (FRED)

( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)

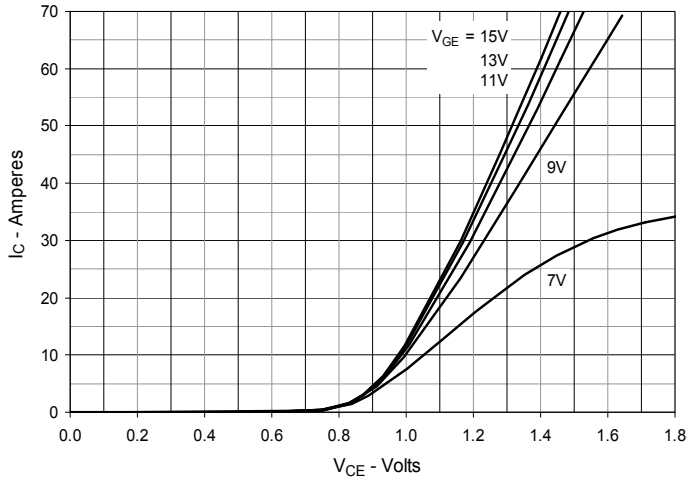
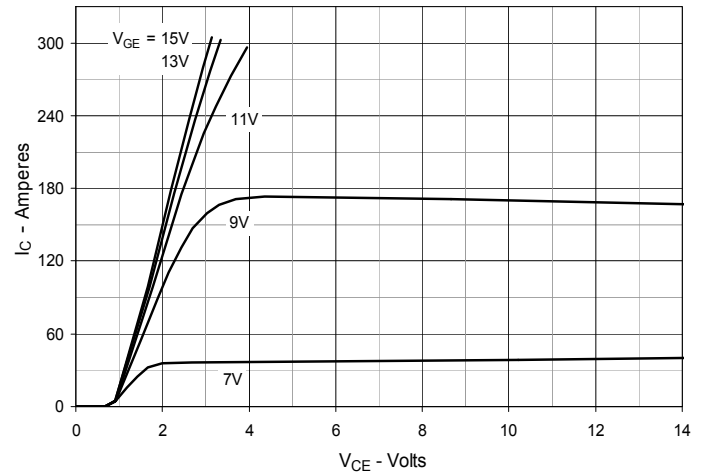
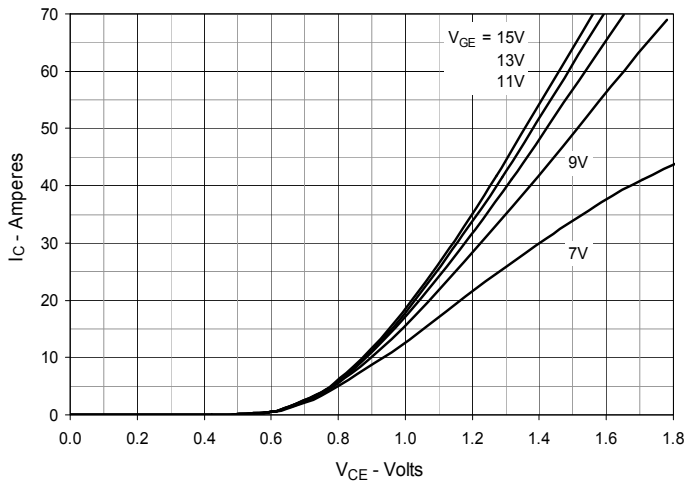
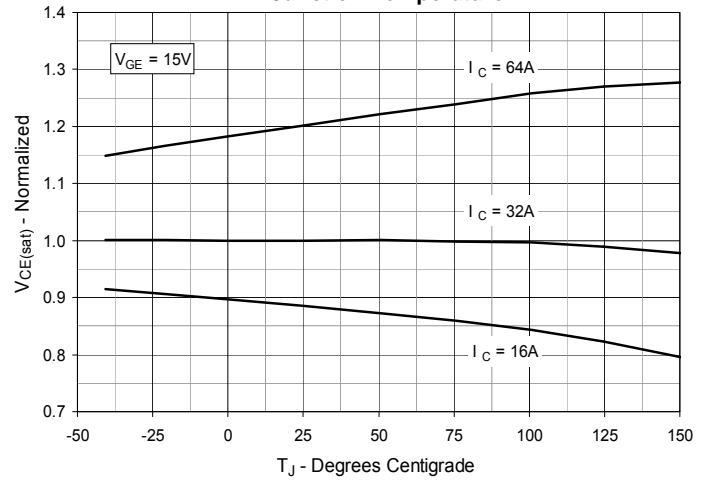
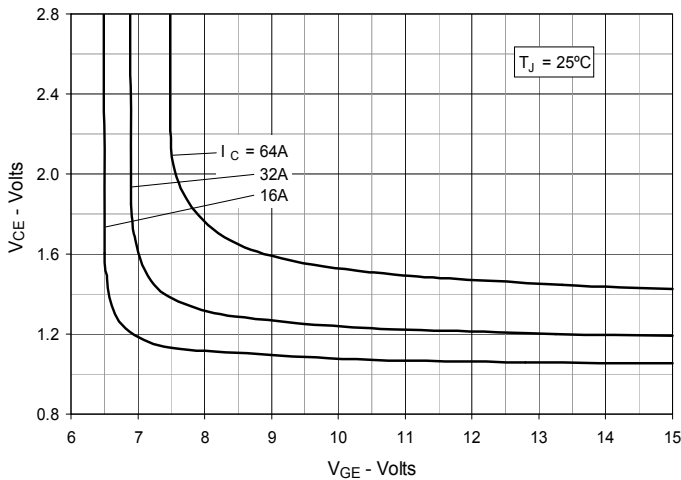
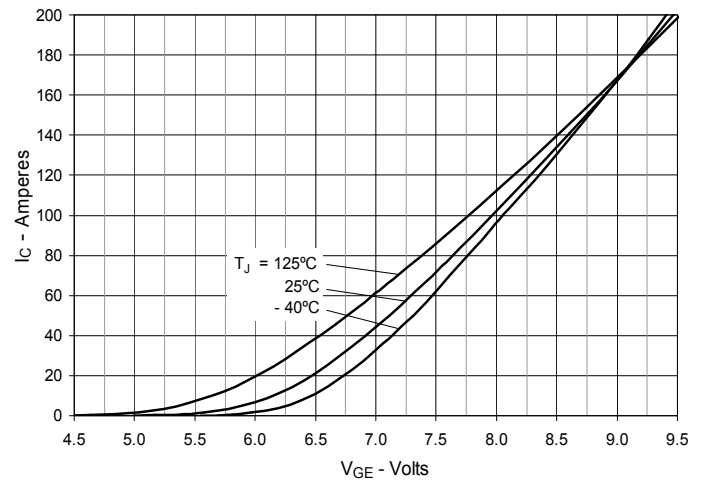
Symbol	Test Conditions	Characteristic Value		
		Min.	Typ.	Max.
$V_F$	$I_F = 30\text{A}, V_{GE} = 0\text{V}$ , Note 1			3.0 V
		$T_J = 150^\circ\text{C}$	1.6	V
$I_{RM}$	$I_F = 30\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$ , $T_J = 100^\circ\text{C}$			4 A
$t_{rr}$	$V_R = 300\text{V}$ , $T_J = 100^\circ\text{C}$		100	ns
	$I_F = 1\text{A}, V_R = 30\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		25	ns
$R_{thJC}$				0.9 $^\circ\text{C/W}$

### Notes:

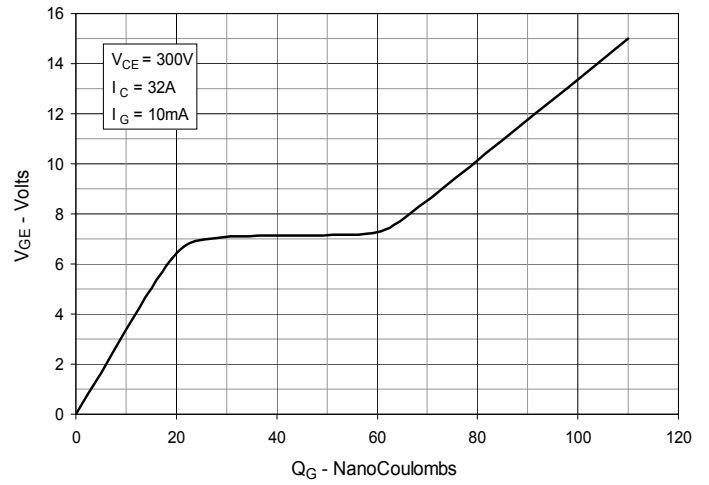
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$ (clamp),  $T_J$  or  $R_G$ .

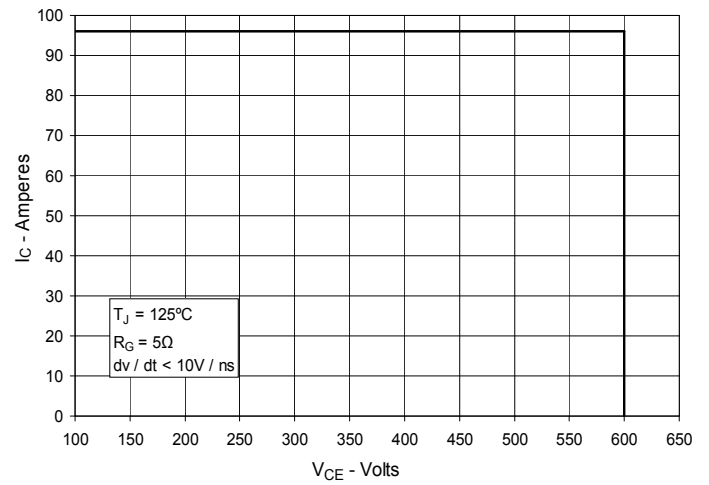
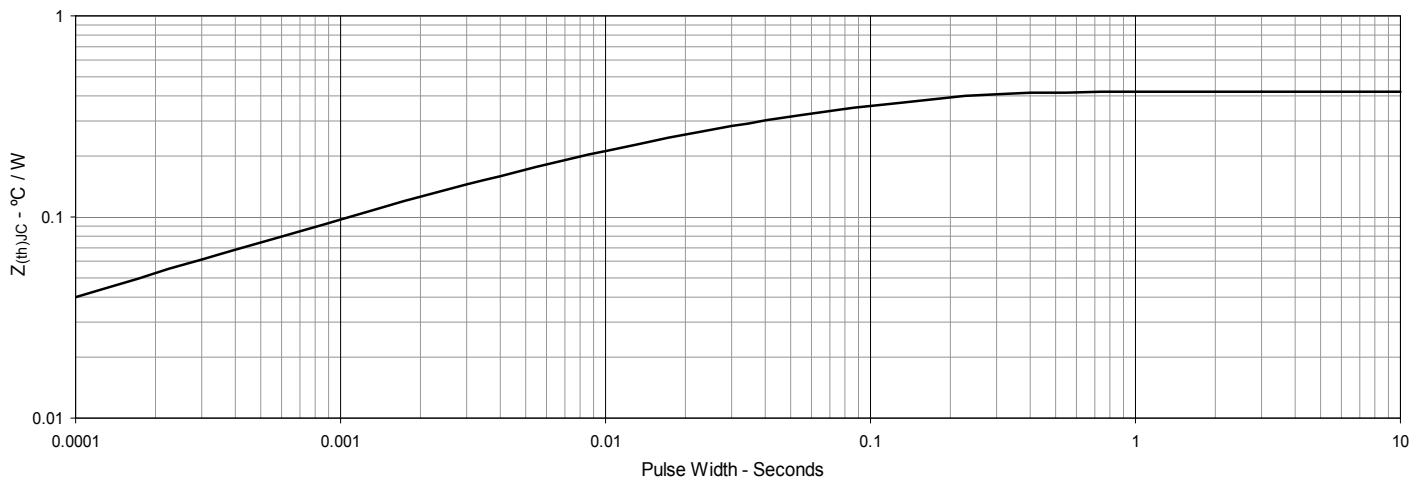
IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


**Fig. 7. Transconductance**

**Fig. 8. Gate Charge**

**Fig. 9. Capacitance**

**Fig. 10. Reverse-Bias Safe Operating Area**

**Fig. 11. Maximum Transient Thermal Impedance**


**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



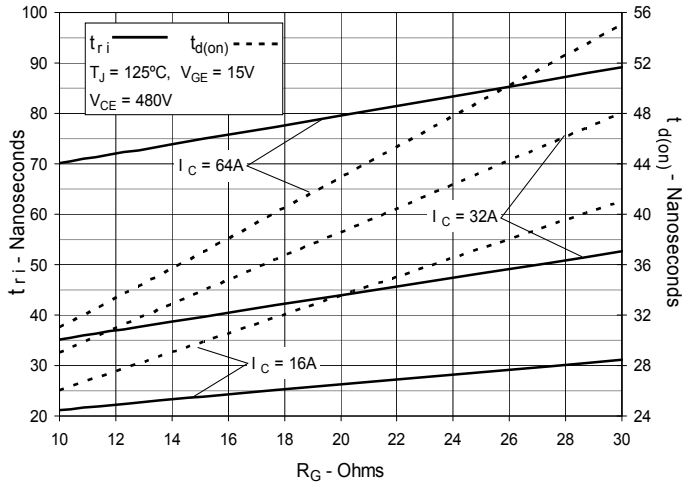
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



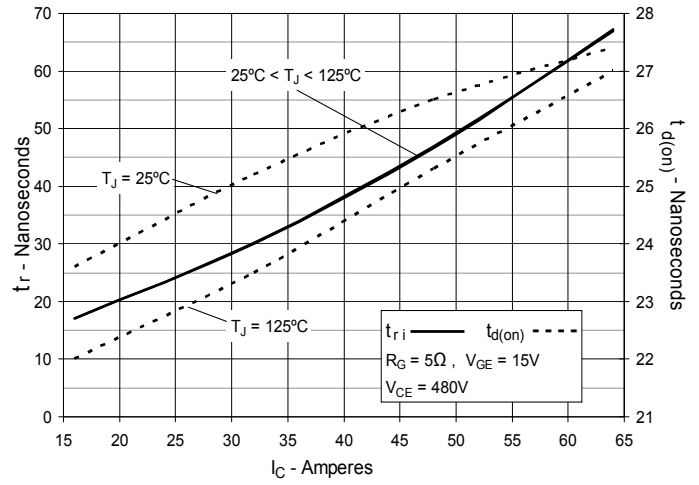
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**

